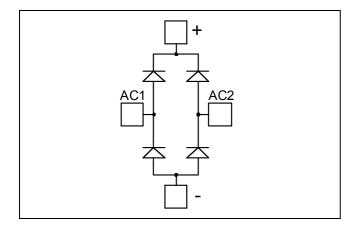


Diode Full Bridge Power Module

 $V_{RRM} = 1000V$ $I_C = 200A$ @ Tc = 70°C

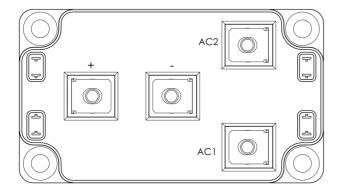


Application

- Uninterruptible Power Supply (UPS)
- Induction heating
- Welding equipment
- High speed rectifiers

Features

- Ultra fast recovery times
- Soft recovery characteristics
- High blocking voltage
- High current
- Low leakage current
- Very low stray inductance
 - Symmetrical design
 - M5 power connectors
- High level of integration



Benefits

- Outstanding performance at high frequency operation
- Low losses
- Low noise switching
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- RoHS Compliant

All ratings @ $T_j = 25$ °C unless otherwise specified

Absolute maximum ratings

Symbol	Parameter			Max ratings	Unit	
V_R	Maximum DC reverse Voltage			1000	V	
V_{RRM}	Maximum Peak Repetitive Revers	e Voltage	1000	V		
T	Maximum Average Forward	Duty avala	- 500/	$T_C = 25^{\circ}C$	255	
$\mathbf{I}_{\mathrm{F(AV)}}$	Current	Duty cycle =	- 30%	$T_C = 70$ °C	200	Α
I _{F(RMS)}	RMS Forward Current	Duty cycle = 50%		$T_C = 45^{\circ}C$	255	А
I_{FSM}	Non-Repetitive Forward Surge Cu	rrent 8	rent 8.3ms $T_C = 45 ^{\circ}\text{C}$		1500	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{F}	Diode Forward Voltage	$I_F = 200A$			2.1	2.7	V
		$I_F = 300A$			2.3		
		$I_F = 200A$	$T_{j} = 125^{\circ}C$		1.7		
I_{RM}	Maximum Reverse Leakage Current	$V_{\rm p} = 1000 {\rm V}$	$T_i = 25^{\circ}C$			100	4
			$T_j = 125$ °C			600	μΑ
C_{T}	Junction Capacitance	$V_R = 1000V$			240		pF

Dynamic Characteristics

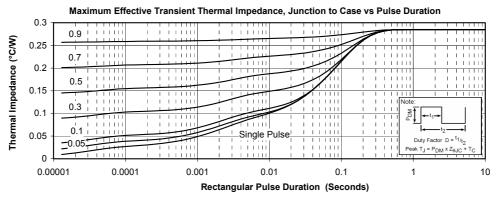
Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
t_{rr}	Reverse Recovery Time	$I_F=1A, V_R=30V$ $di/dt = 200A/\mu s$	$T_j = 25$ °C		43		ns
t_{rr}	Reverse Recovery Time		$T_j = 25^{\circ}C$		290		- ns
ι _{rr}			$T_j = 125^{\circ}C$		340		
Q _{rr}	Reverse Recovery Charge	$I_F = 200A$ $V_R = 667V$	$T_j = 25^{\circ}C$		1.37		μС
Qrr	Reverse Recovery Charge	$di/dt = 400A/\mu s$	$T_{j} = 125^{\circ}C$		8.1		μС
Inne	Reverse Recovery Current	Reverse Recovery Current	$T_j = 25^{\circ}C$		12		A
I_{RRM}	Reverse Recovery Current		$T_{j} = 125^{\circ}C$		36		
t_{rr}	Reverse Recovery Time	$I_F = 200A$ $V_R = 667V$ $di/dt = 2000A/\mu s$			160		ns
Qrr	Reverse Recovery Charge		$T_j = 125$ °C		14.2		μС
I_{RRM}	Reverse Recovery Current				140		A

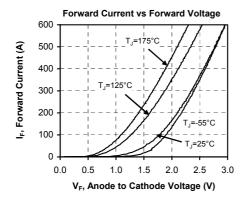
Thermal and package characteristics

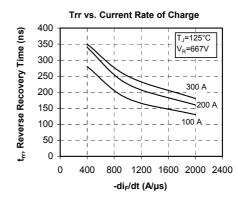
Symbol	Characteristic			Min	Typ	Max	Unit
R_{thJC}	Junction to Case Thermal Resistance					0.285	°C/W
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T_{J}	Operating junction temperature range			-40		175	°C
T_{STG}	Storage Temperature Range			-40		125	
$T_{\rm C}$	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
	Mounting torque	For terminals	M5	2		3.5	11.111
Wt	Package Weight					300	g

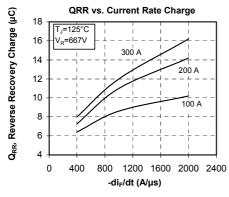


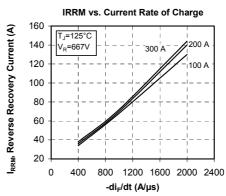
Typical Performance Curve

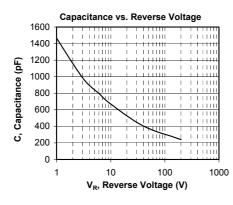


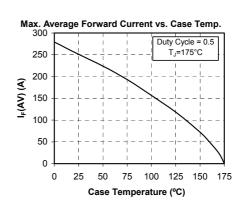








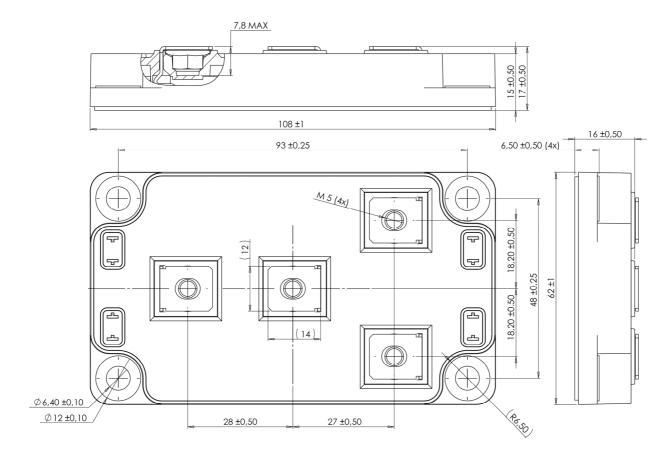




3 - 5



SP6 Package outline (dimensions in mm)





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